

Title (en)
SILICON BASED CHARGE NEUTRALIZATION SYSTEMS

Title (de)
SILICIUMBASIERTE LADUNGSNEUTRALISIERUNGSSYSTEME

Title (fr)
SYSTÈMES DE NEUTRALISATION DE CHARGE À BASE DE SILICIUM

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Abstract (en)
[origin: WO2016153755A1] An embodiment of the invention provides a method for low emission charge neutralization, comprising: generating a high frequency alternating current (AC) voltage; transmitting the high frequency AC voltage to at least one non-metallic emitter (300a); wherein the at least one non-metallic emitter comprises at least 70% silicon by weight and less than 99.99% silicon by weight; wherein the at least one emitter comprises at least one treated surface section (310a) with a destroyed oxidation layer; and generating ions from the at least one non-metallic emitter in response to the high frequency AC voltage. Another embodiment of the invention provides an apparatus for low emission charge neutralization wherein the apparatus can perform the above-described operations.

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